

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max $T_A = +25^\circ C$
80V	16.5mΩ @ $V_{GS} = 10V$	9.7A
	20mΩ @ $V_{GS} = 4.5V$	8.8A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

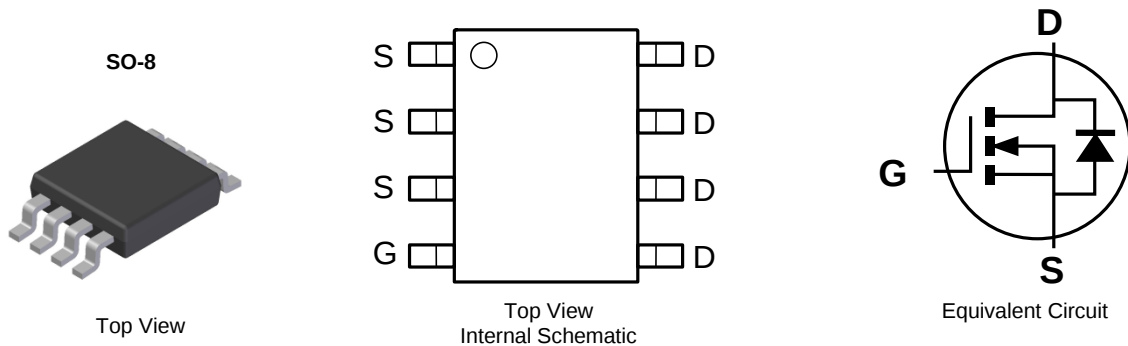
Description and Applications

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in:

- Notebook Battery Power Management
- Loadswitches
- Backlighting
- Power Management Functions
- DC-DC Converters

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.074 grams (Approximate)

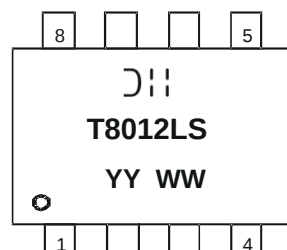


Ordering Information (Note 4)

Part Number	Case	Packaging
DMT8012LSS-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



JII = Manufacturer's Marking
 T8012LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 16 = 2016)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	80	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	9.7 7.8	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	11.6 9.3	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	80	A
Avalanche Current, L=0.1mH			I _{AS}	11.6	A
Avalanche Energy, L=0.1mH			E _{AS}	10.2	mJ

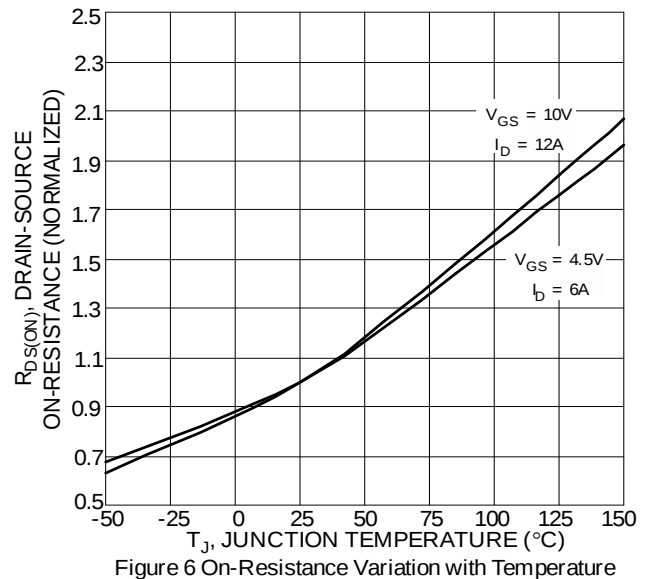
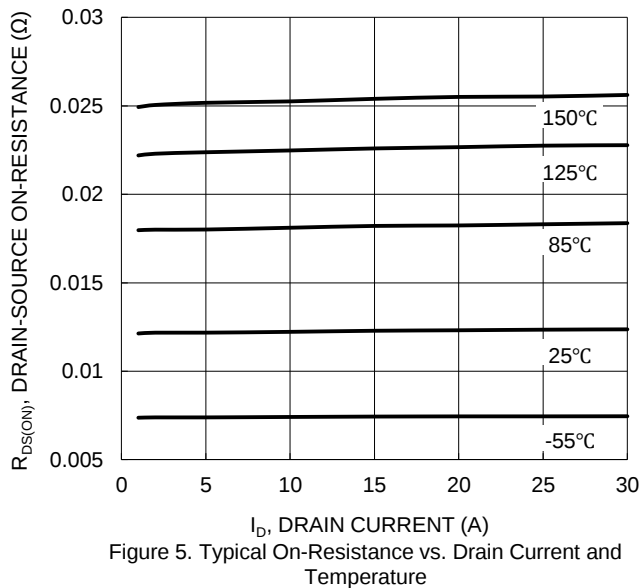
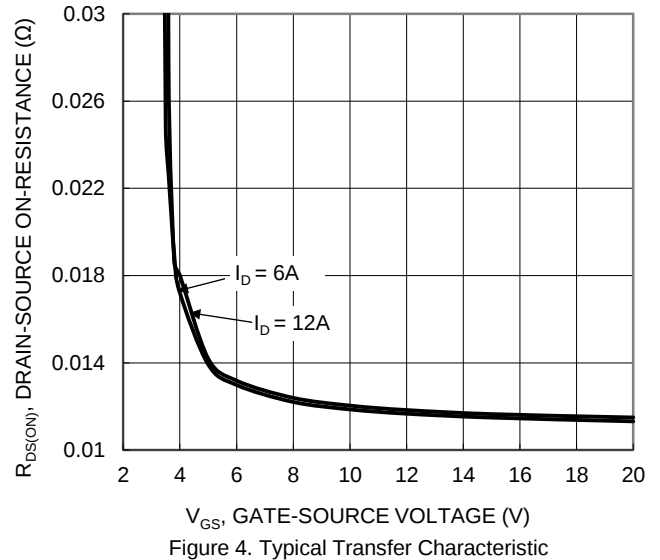
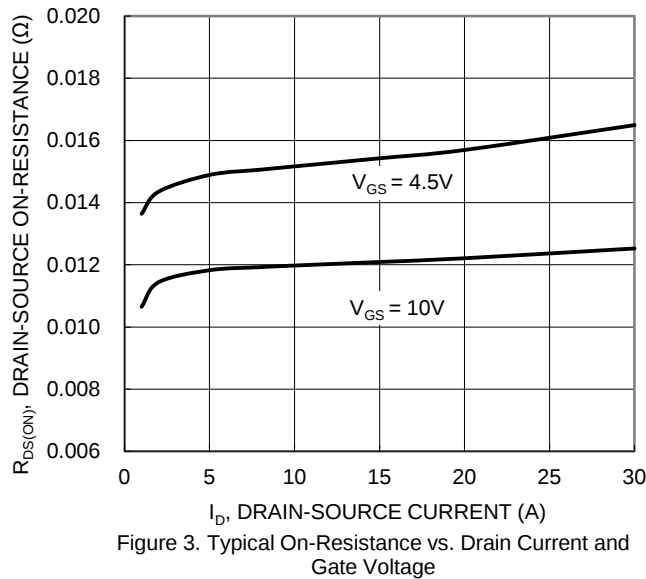
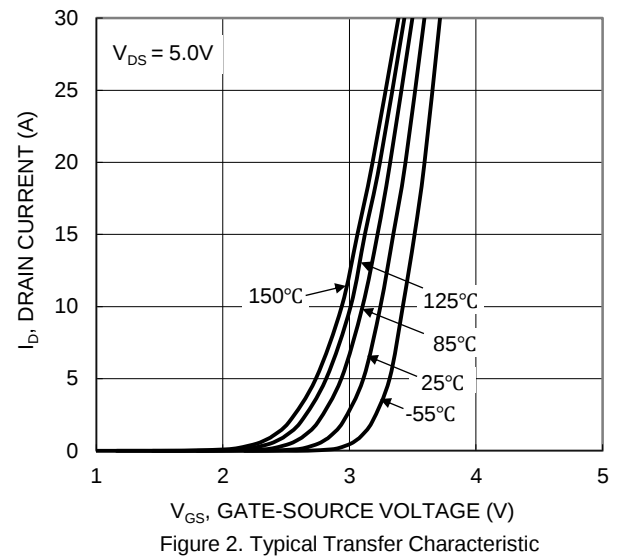
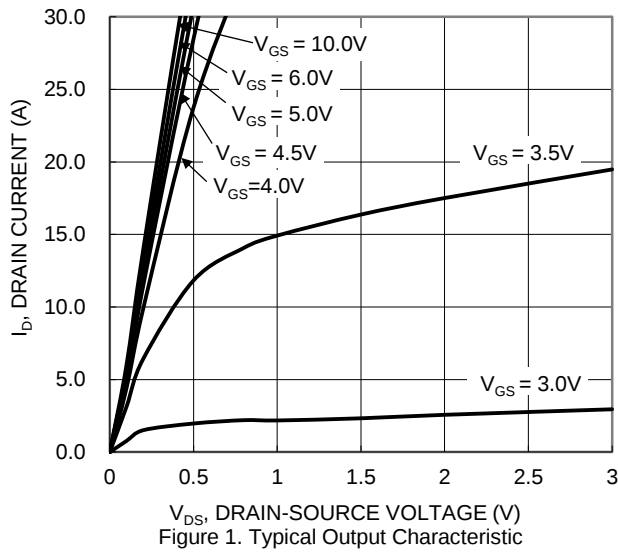
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

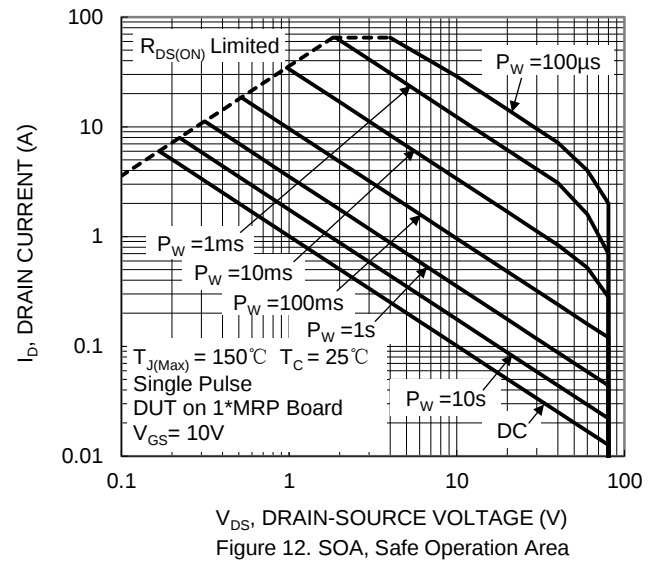
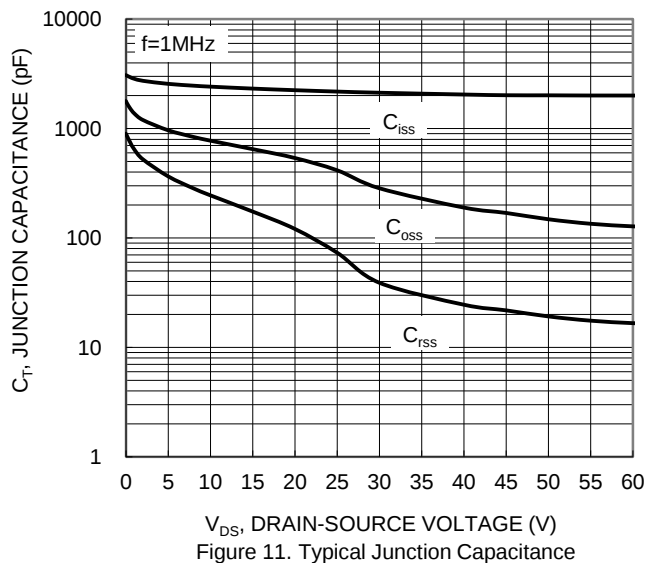
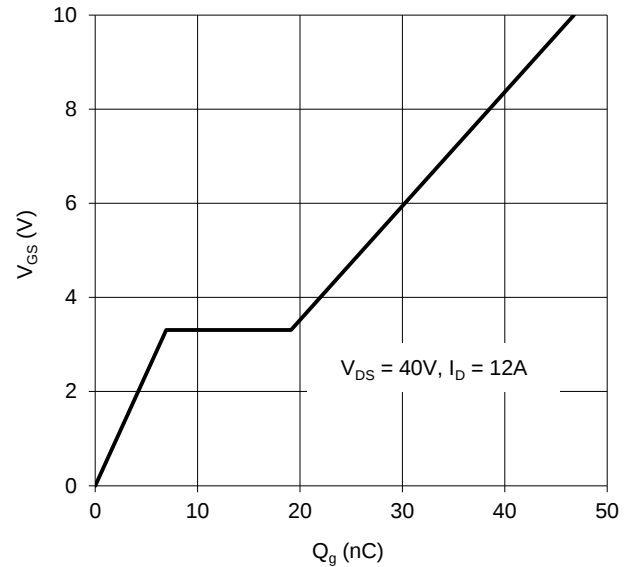
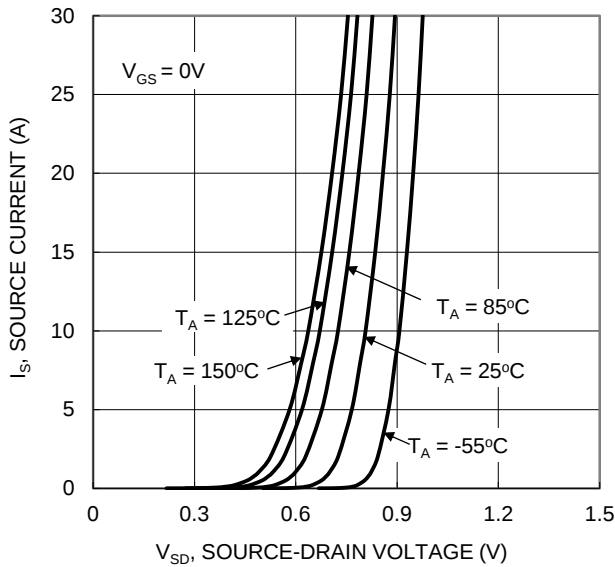
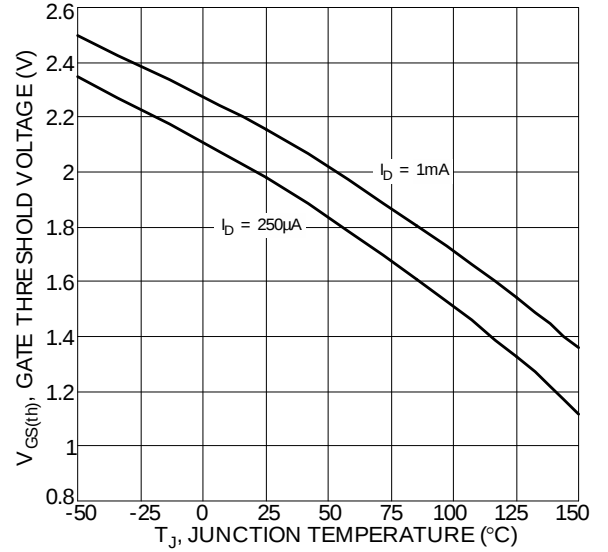
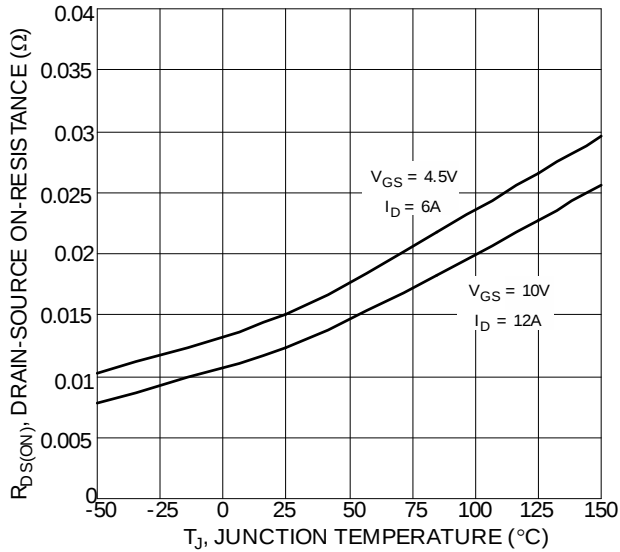
Characteristic			Symbol	Value	Units
Total Power Dissipation (Note 5)			P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	80	°C/W
	t < 10s			48	°C/W
Total Power Dissipation (Note 6)			P _D	2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	53	°C/W
	t < 10s			37	°C/W
Thermal Resistance, Junction to Case (Note 6)			R _{θJC}	6.5	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	80	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 64V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	12.7	16.5	mΩ	V _{GS} = 10V, I _D = 12A
		—	15	20		V _{GS} = 4.5V, I _D = 6A
Diode Forward Voltage	V _{SD}	—	0.9	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	—	1,949	—	pF	V _{DS} = 40V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	—	177	—		
Reverse Transfer Capacitance	C _{RSS}	—	10	—		
Gate Resistance	R _G	—	0.7	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	15	—	nC	V _{DS} = 40V, I _D = 12A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	34	—		
Gate-Source Charge	Q _{GS}	—	6	—		
Gate-Drain Charge	Q _{GD}	—	4.5	—		
Turn-On Delay Time	t _{D(ON)}	—	4.9	—	ns	V _{DD} = 40V, V _{GS} = 10V, I _D = 12A, R _G = 1.6Ω
Turn-On Rise Time	t _R	—	3.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	16.5	—		
Turn-Off Fall Time	t _F	—	3.5	—		

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz. copper, with 1-inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.





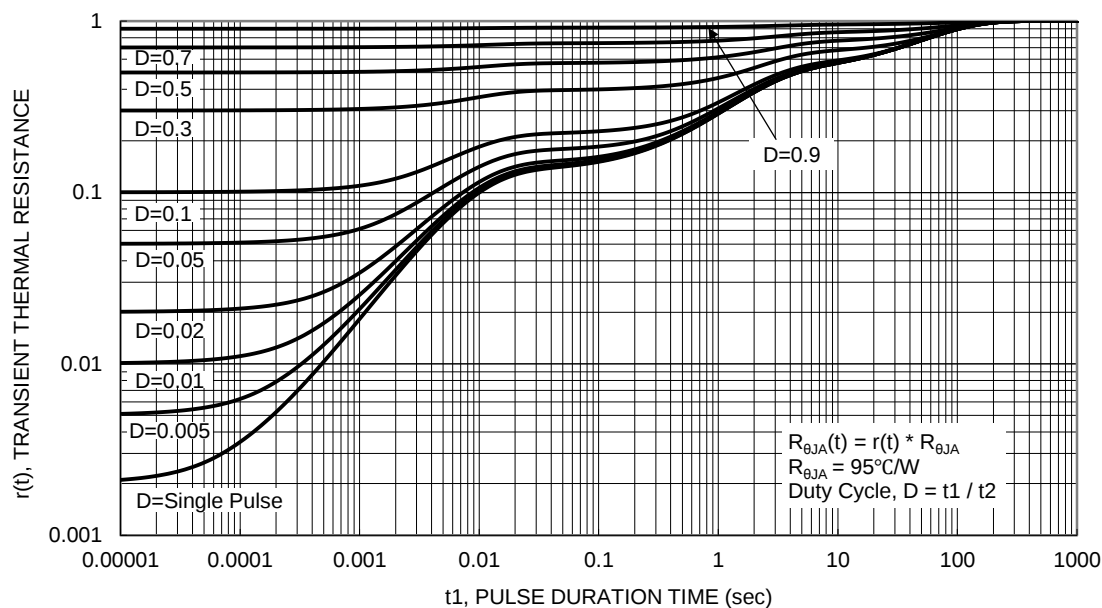
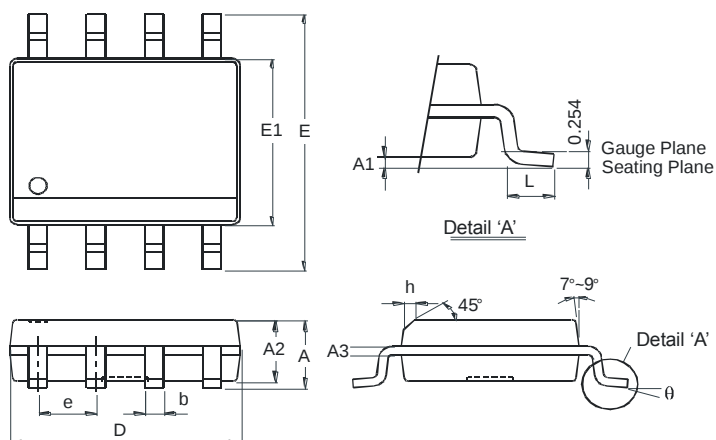


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

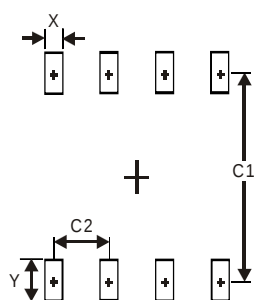


SO-8		
Dim	Min	Max
A	–	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	–	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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